

## General Description

The WSP4067 is the highest performance trench N-ch and P-ch MOSFET with extreme high cell density, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications.

The WSP4067 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

## Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
$V_{DS}$	Drain-Source Voltage	40	-40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.5	-5.5	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6	-4.5	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	30	-20	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	25	25	mJ
$I_{AS}$	Avalanche Current	10	10	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	2	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	150	150	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62.5	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	50	$^\circ C/W$

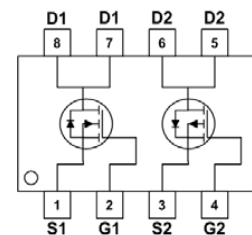
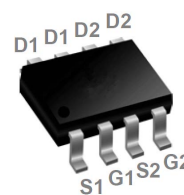
## Product Summary

BVDSS	RDS(on)	ID
40V	21m $\Omega$	7.5A
-40V	38m $\Omega$	-5.5A

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter.
- Networking DC-DC Power System
- Load Switch

## SOP-8 Pin Configuration



**N-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.067	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	---	16	21	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	18	25	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.5	2	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.24	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	1	uA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	30	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =8A	---	24	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2.5	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A	---	15.7	22	nC
Q <sub>gs</sub>	Gate-Source Charge		---	3.24	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.75	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =20V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω, I <sub>D</sub> =1A, R <sub>L</sub> =20Ω	---	7.8	---	ns
T <sub>r</sub>	Rise Time		---	6.9	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	22.4	---	
T <sub>f</sub>	Fall Time		---	4.8	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	---	815	---	pF
C <sub>oss</sub>	Output Capacitance		---	95	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	60	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =25V, L=0.1mH, I <sub>AS</sub> =16A	11.2	---	---	mJ

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	6.0	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	24	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1.7A, T <sub>J</sub> =25°C	---	---	1.1	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=16A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

**P-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-40	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.03	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.5A	---	30	38	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.5A	---	46	62	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.5	-2.0	-2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4.56	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	-1	uA
		V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	-30	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4.5A	---	18	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	8	---	Ω
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.5A	---	7.5	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.4	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.5	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-20V, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω, I <sub>D</sub> =-1A, R <sub>L</sub> =20Ω.	---	8.7	---	ns
T <sub>r</sub>	Rise Time		---	7	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	31	---	
T <sub>f</sub>	Fall Time		---	17	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	668	---	pF
C <sub>oss</sub>	Output Capacitance		---	98	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	72	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =-25V, L=0.1mH, I <sub>AS</sub> =-18A	11	---	---	mJ

**Diode Characteristics**

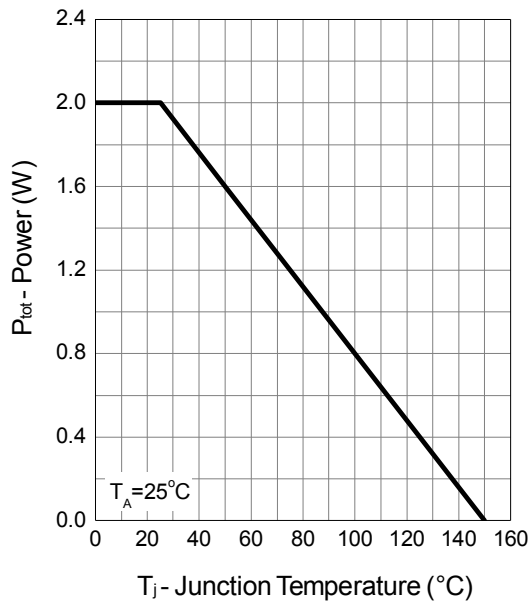
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-5.5	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	-20	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.1	V

Note :

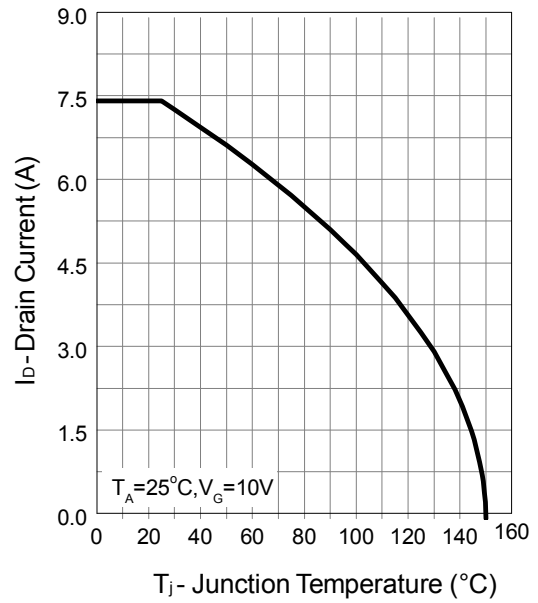
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper,t<10sec.
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- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

**N-Channel Typical Characteristics**

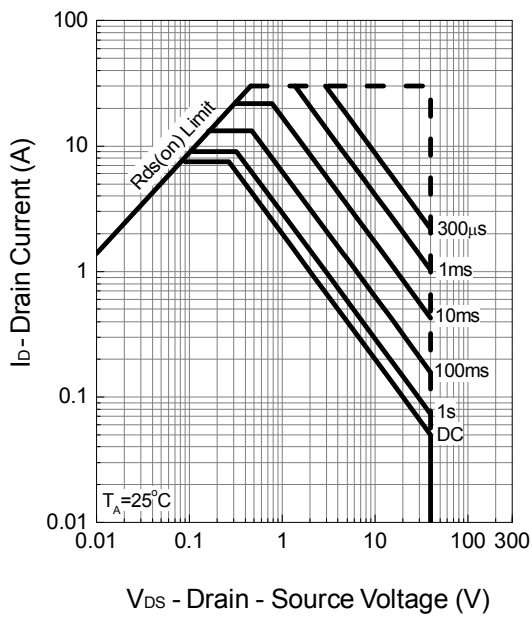
**Power Dissipation**



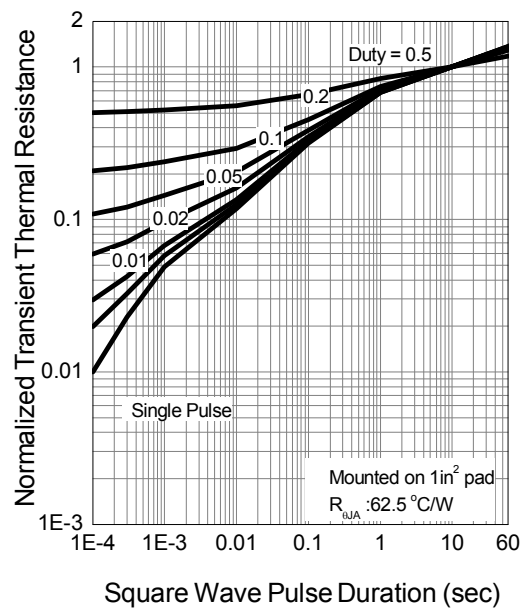
**Drain Current**



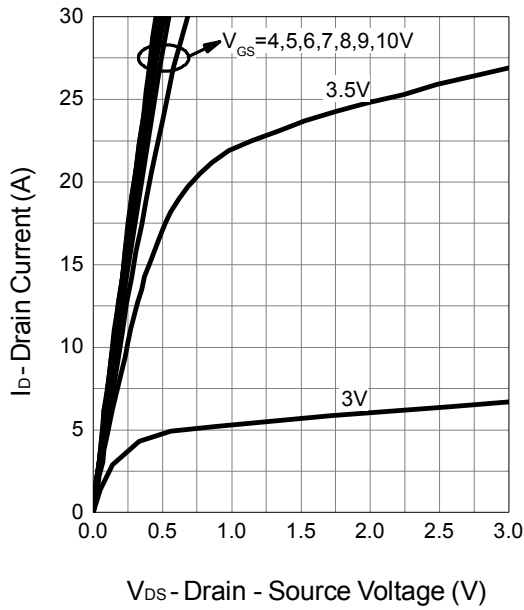
**Safe Operation Area**



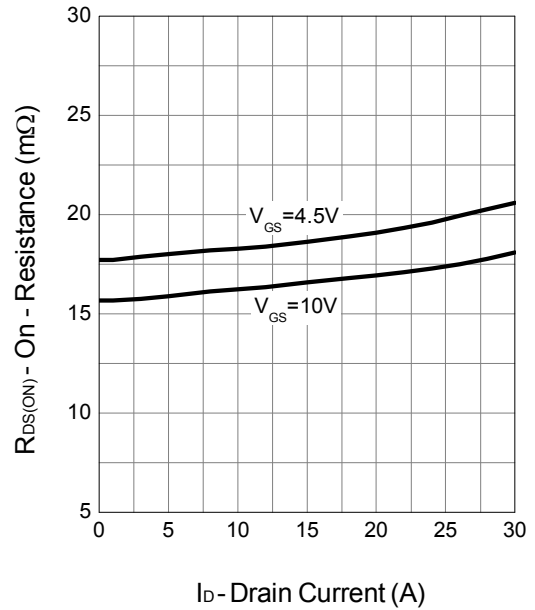
**Thermal Transient Impedance**



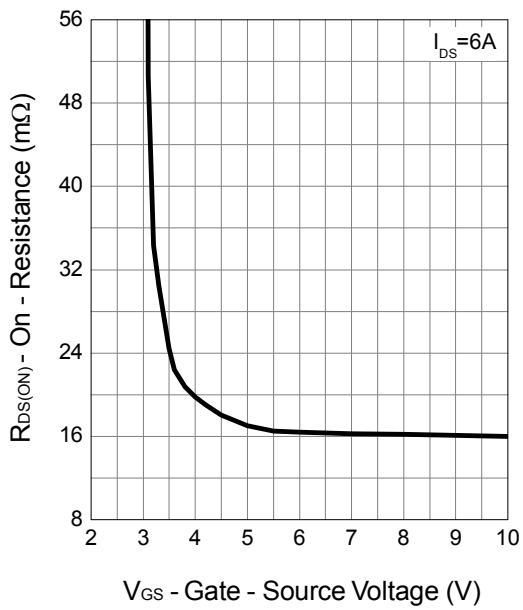
**Output Characteristics**



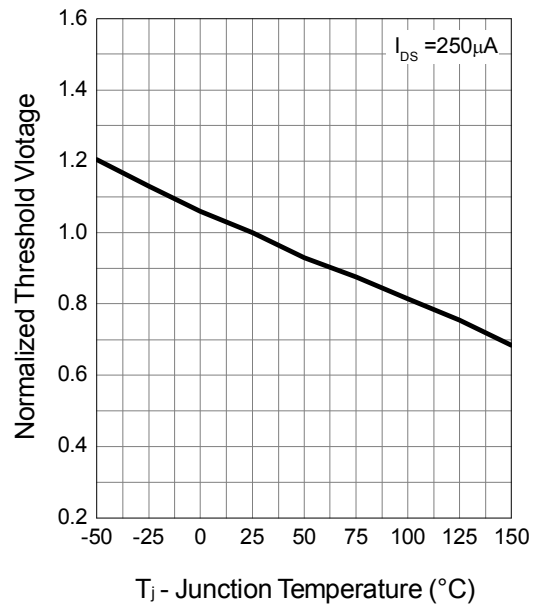
**Drain-Source On Resistance**



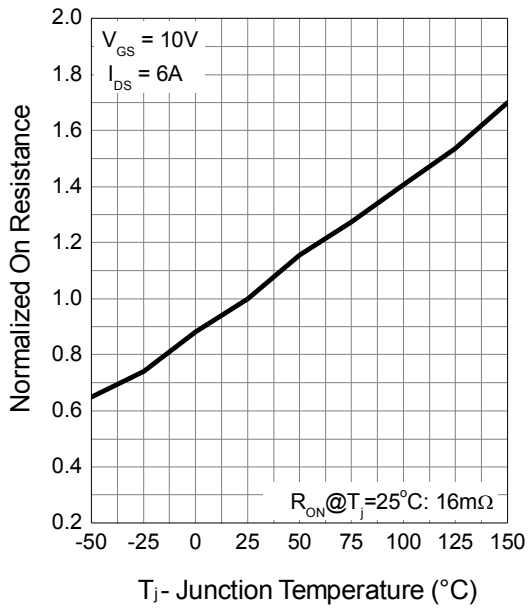
**Gate-Source On Resistance**



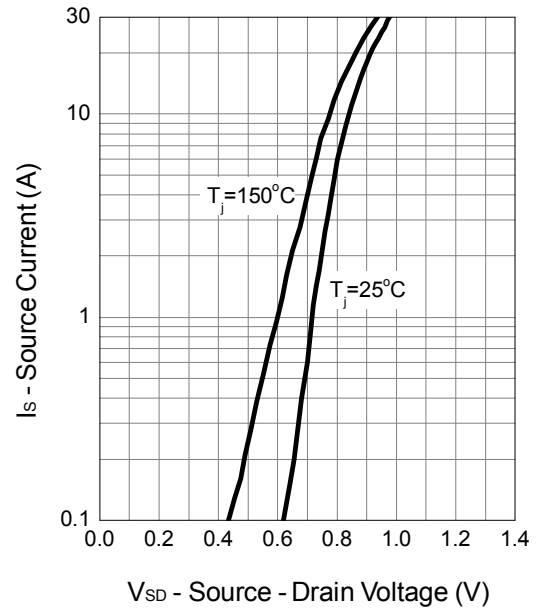
**Gate Threshold Voltage**



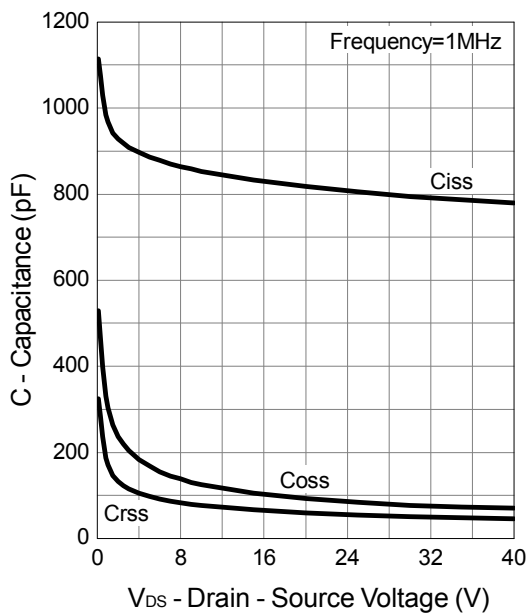
**Drain-Source On Resistance**



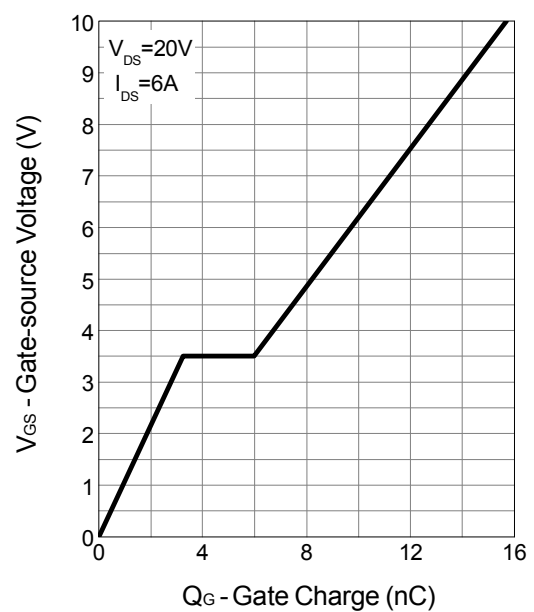
**Source-Drain Diode Forward**



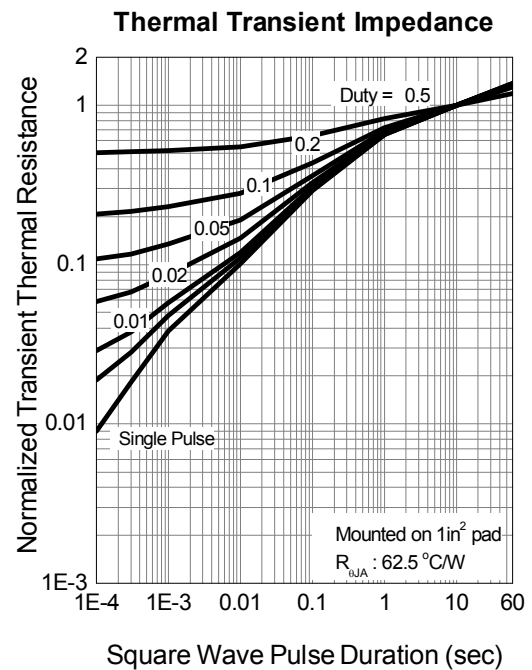
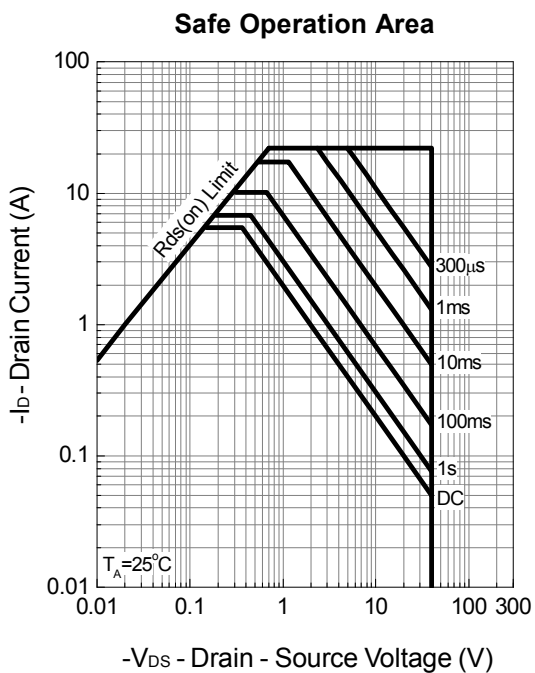
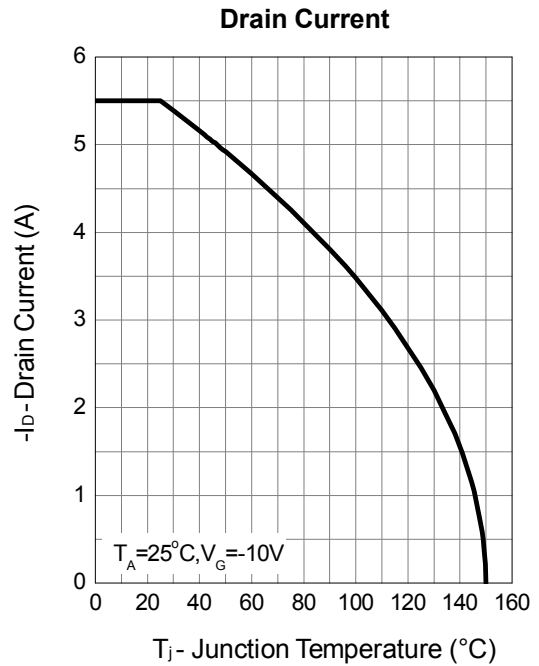
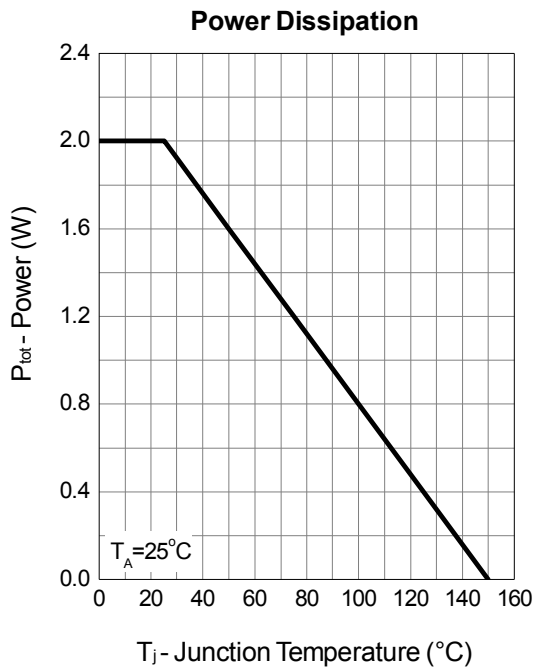
**Capacitance**



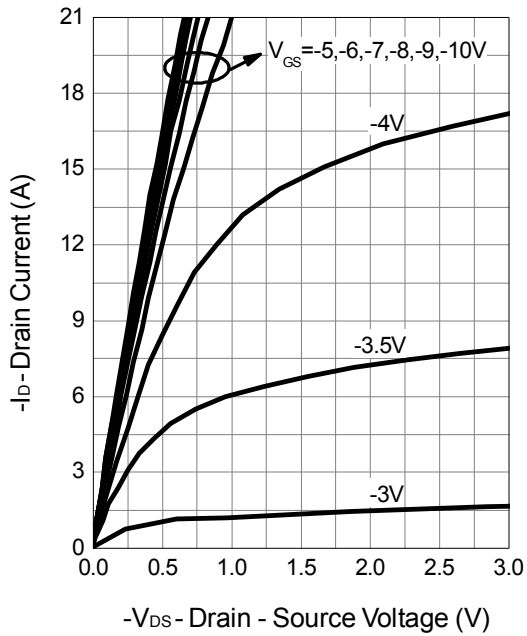
**Gate Charge**



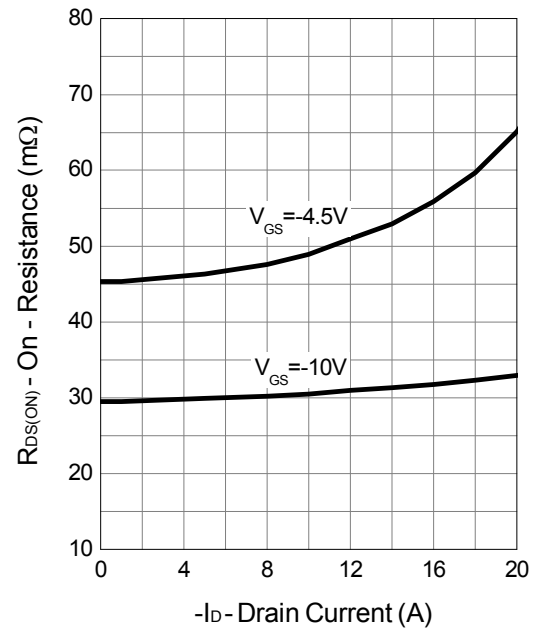
**P-Channel Typical Characteristics**



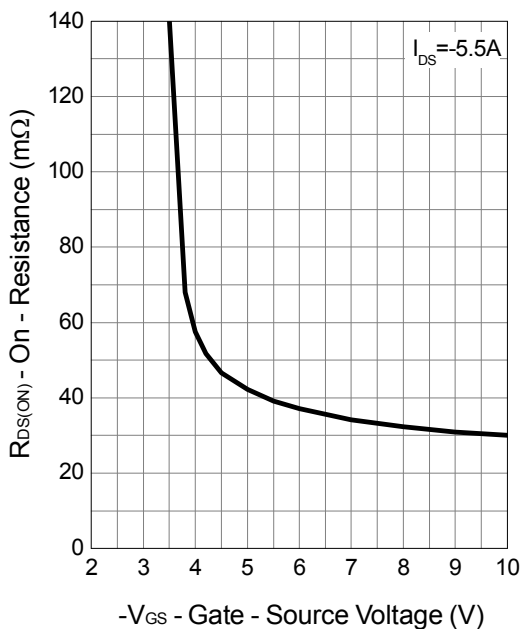
**Output Characteristics**



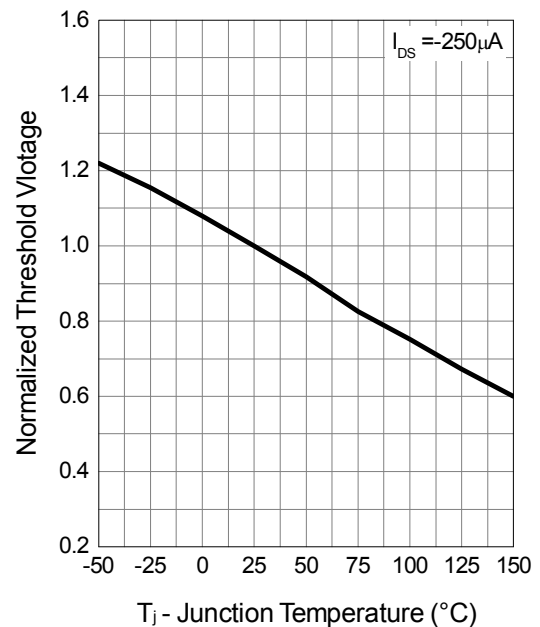
**Drain-Source On Resistance**



**Gate-Source On Resistance**

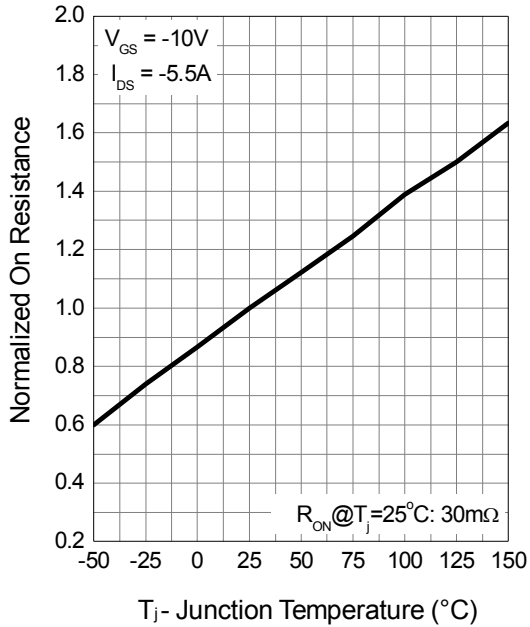


**Gate Threshold Voltage**

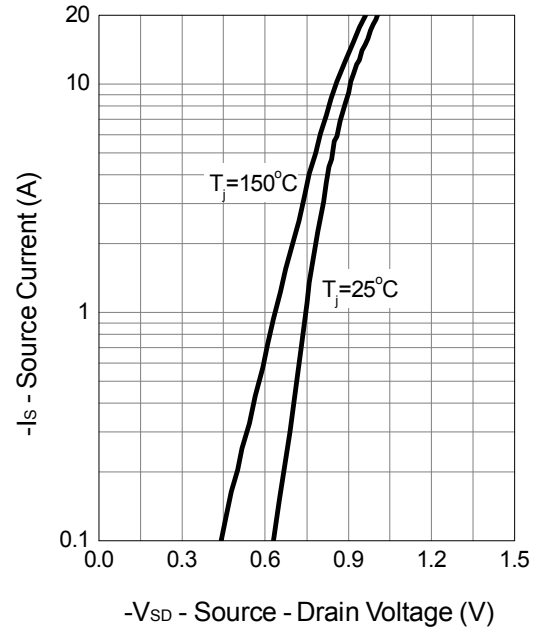




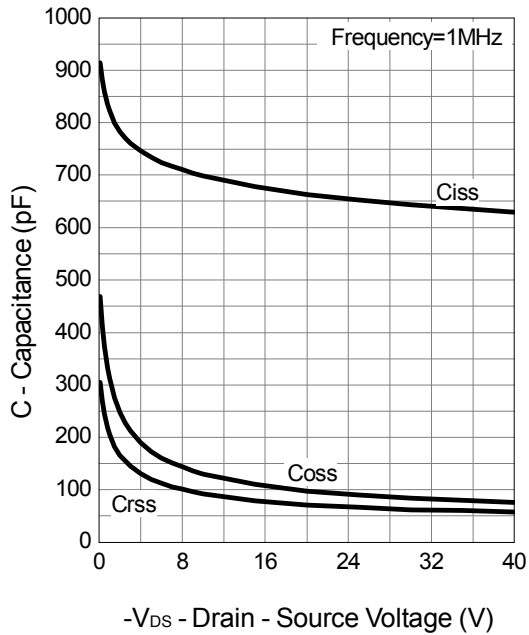
**Drain-Source On Resistance**



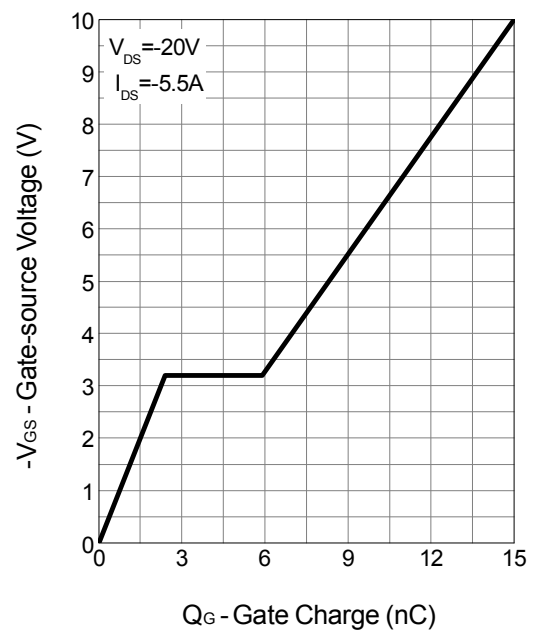
**Source-Drain Diode Forward**



**Capacitance**



**Gate Charge**





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